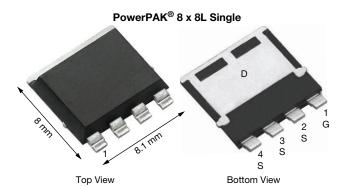
SQJQ466E

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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET



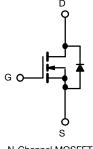
PRODUCT SUMMARY	
V _{DS} (V)	60
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0019
I _D (A)	200
Configuration	Single
Package	PowerPAK 8 x 8L

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



FREE



N-Channel MOSFET

ABSOLUTE MAXIMUM RATIN	GS (T _C = 25 °C, unless	otherwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current	T _C = 25 °C ª	1	200		
Continuous drain current	T _C = 125 °C	I _D	118		
Continuous source current (diode conduct	ion)	۱ _S	200	А	
Pulsed drain current ^b		I _{DM}	500		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	75		
Single pulse avalanche energy		E _{AS}	281	mJ	
Maximum power dissipation	T _C = 25 °C	D	150	W	
Maximum power dissipation	T _C = 125 °C	P _D	50	vv	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temper	ature) ^{d, e}		260	C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	50	°C/W
Junction-to-case (drain)		R _{thJC}	1	0/10

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	60	-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3	3.5	v
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V_{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	100	-	-	Α
		V _{GS} = 10 V	I _D = 10 A	-	0.0017	0.0019	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	0.0030	Ω	
		$V_{GS} = 10 V$	I _D = 10 A, T _J = 175 °C	-	-	0.0035	
Forward transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		-	140	-	S
Dynamic ^b		•					
Input capacitance	C _{iss}			-	8170	10 210	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	3756	4700	pF
Reverse transfer capacitance	C _{rss}			-	70	88	
Total gate charge ^c	Qg			-	135	180	
Gate-source charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	-	47	-	nC
Gate-drain charge ^c	Q _{gd}			-	14	-	
Gate resistance	Rg	f = 1 MHz		0.5	0.9	1.5	Ω
Turn-on delay time ^c	t _{d(on)}			-	24	30	
Rise time ^c	t _r	V _{DD}	= 30 V, R_L = 3 Ω	-	8	10]
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 10 \text{ A},$	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	47	58	ns
Fall time ^c	t _f	1		-	15	19	1
Source-Drain Diode Ratings and Ch	aracteristics ^b	•			•		
Pulsed current ^a	I _{SM}			-	-	300	Α
Forward voltage	V _{SD}	l _F :	= 50 A, V _{GS} = 0	-	0.82	1.2	V

Notes

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

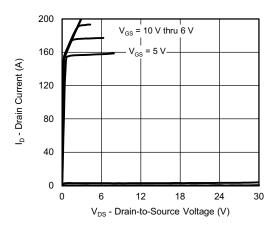
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

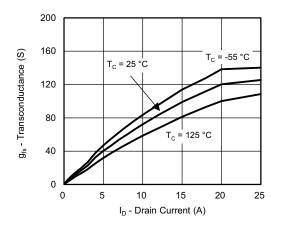


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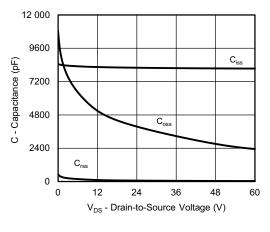
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



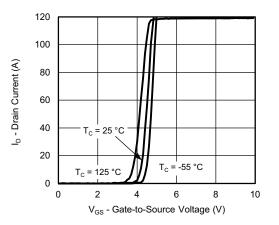
Output Characteristics



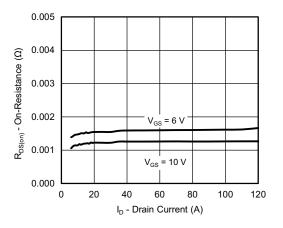
Transconductance



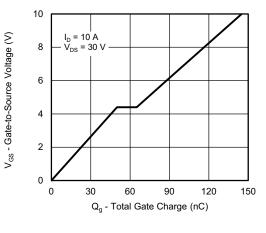
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

S16-2420-Rev. A, 28-Nov-16

3 stions contact: automostechsup Document Number: 75138

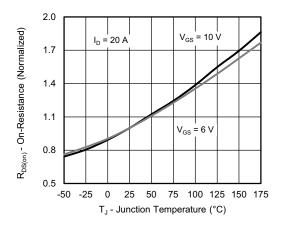
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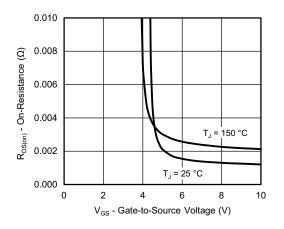
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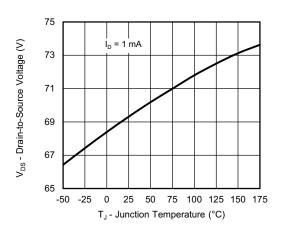
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



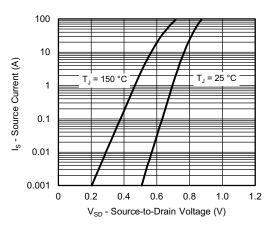
On-Resistance vs. Junction Temperature



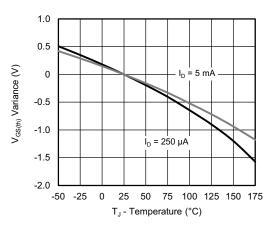
On-Resistance vs. Gate-to-Source Voltage



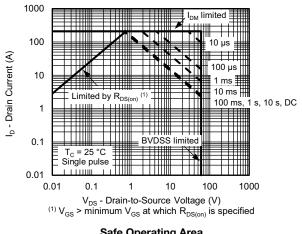
Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



Threshold Voltage



Safe Operating Area

S16-2420-Rev. A, 28-Nov-16

4

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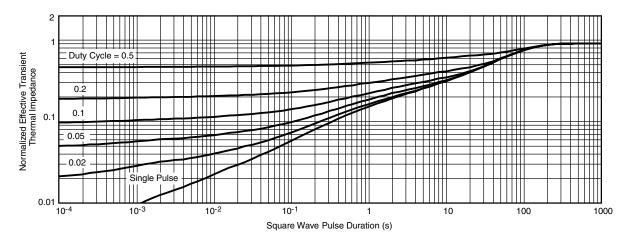
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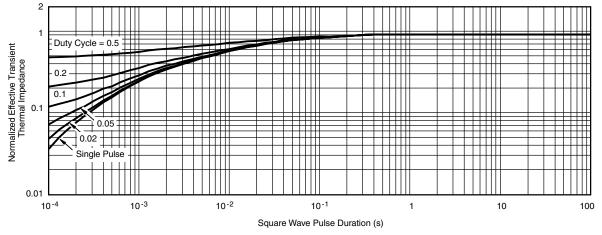
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



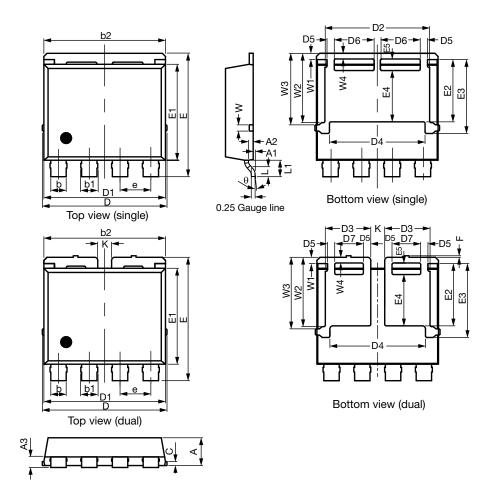
Normalized Thermal Transient Impedance, Junction-to-Case

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DIM.		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.70	1.80	1.90	0.067	0.071	0.075	
A1	0.00	0.08	0.13	0.000	0.003	0.005	
A2	0.25	0.30	0.35	0.010	0.012	0.014	
A3	0.55	0.62	0.70	0.022	0.024	0.028	
b	0.92	1.00	1.08	0.036	0.039	0.043	
b1	1.02	1.10	1.18	0.040	0.043	0.046	
b2	7.80	7.90	8.00	0.307	0.311	0.315	
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	8.00	8.10	8.25	0.315	0.319	0.325	
D1	7.80	7.90	8.00	0.307	0.311	0.315	
D2	6.70	6.80	6.90	0.264	0.268	0.272	
D3	2.85	2.95	3.05	0.112	0.116	0.120	
D4	6.11	6.21	6.31	0.241	0.244	0.248	
D5	0.37	0.47	0.57	0.015	0.019	0.022	
D6	2.49	2.59	2.69	0.098	0.102	0.106	
D7	1.76	1.86	1.96	0.069	0.073	0.077	

Revision: 16-Oct-17

Document Number: 67734

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Package Information





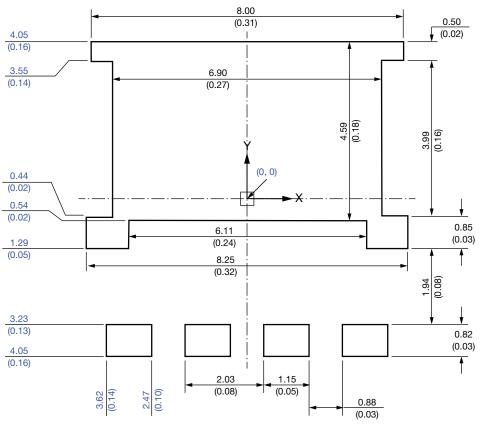
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DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
е	1.95	2.00	2.05	0.077	0.079	0.081	
Е	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	3.94	4.04	4.14	0.140	0.159	0.163	
E3	4.69	4.79	4.89	0.185	0.189	0.193	
E4	3.23	3.33	3.43	0.127	0.131	0.135	
E5	0.65	0.75	0.85	0.026	0.030	0.033	
F	0.00	0.10	0.15	0.000	0.004	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К	0.80	0.90	1.00	0.031	0.035	0.039	
W	0.30	0.40	0.50	0.012	0.016	0.020	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W2	4.39	4.49	4.59	0.173	0.177	0.181	
W3	4.54	4.64	4.74	0.179	0.183	0.187	
W4	0.32	0.37	0.42	0.013	0.015	0.017	
θ	6°	10°	14°	6°	10°	14°	



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Recommended Minimum PADs for PowerPAK® 8 x 8L Single



Dimensions in millimeters (inches)

Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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